

## High-quality ZnO nanorods based flexible devices for electronic and biological applications

N. Koteeswara Reddy,<sup>1,2</sup> M. Devika,<sup>1,3</sup> C. W. Tu<sup>1,4</sup>

<sup>1</sup>Department of Nanobio Materials and Electronics, Gwangju Institute of Science and Technology, Gwangju 500712, Korea

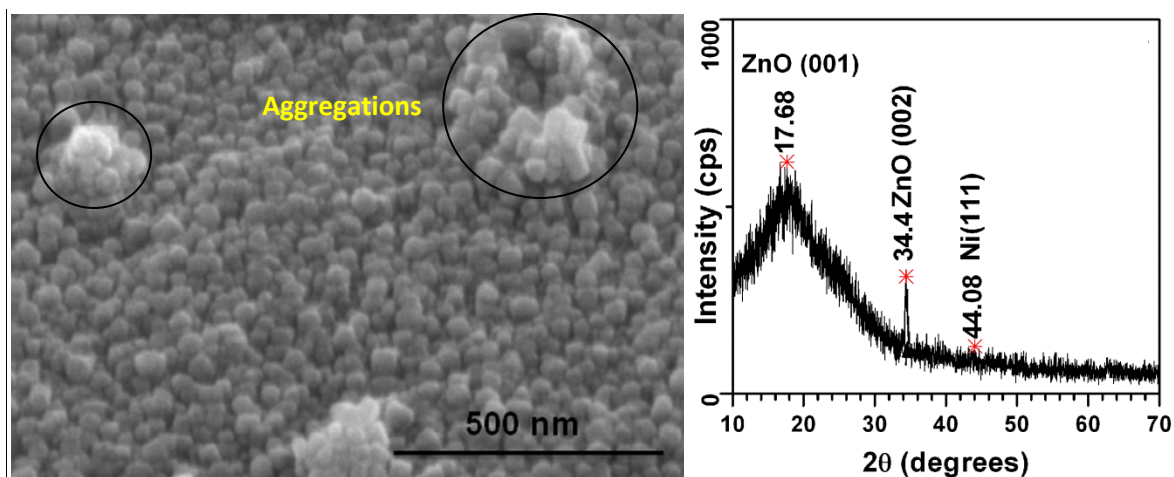
<sup>2</sup>Center for Nanoscience and Engineering, Indian Institute of Science, Bangalore 560012, India

<sup>3</sup>Department of Aerospace Engineering, Indian Institute of Science, Bangalore 560012, India

<sup>4</sup>Department of Electrical and Computer Engineering, University of California, San Diego, La Jolla, California 92093-0407, USA

### Supporting Information

**SI-1:** The ZnO seed-layers deposited under optimized conditions of  $V_c = 1.5$  V and  $A_T = 200$  °C) in the long duration time of  $Dt = 30$  min was examined by SEM and XRD. The SEM image and XRD profile of the as-deposited ZnO seed-layers on Ni coated Kapton sheets are given below.



**SI-2:** XRD profile of ZnO NRs grown on seed-layers deposited at optimized conditions is given below. It shows that the as-synthesized ZnO NRs are preferentially oriented along (001)

planes since the observed d-spacing value of the diffraction peak is about 0.259 nm, which exactly matches with the standard JCPDS data (Card No: 36-1451). Further, the observed single diffraction peak suggests that the as-grown NRs exclusively have single ZnO phase.

